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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
09/521,389	03/08/2000	Shigeru Okamoto	1508.63671	9947
7590 01/13/2004		EXAMINER		
PATRICK G. BURNS, ESQ. GREER,BURNS & CRAIN, LTD. 300 S. WACKER DR. SUITE 2500 CHICAGO, IL 60606			MALDONADO, JULIO J	
			ART UNIT	PAPER NUMBER
			2823	
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Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)			
	09/521,389	OKAMOTO, SHIGERU			
Office Action Summary	Examin r	Art Unit			
	Julio J. Maldonado	2823			
The MAILING DATE of this communication apperiod for Reply	pears on the cover sheet wit	h the correspondence address			
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repl - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statute - Any reply received by the Office later than three months after the mailin earned patent term adjustment. See 37 CFR 1.704(b). Status	136(a). In no event, however, may a re ly within the statutory minimum of thirty will apply and will expire SIX (6) MONT e, cause the application to become AB/	ply be timely filed (30) days will be considered timely. THS from the mailing date of this communication. ANDONED (35 U.S.C. § 133).			
1)⊠ Responsive to communication(s) filed on <u>14 October 2003</u> .					
2a) This action is FINAL . 2b) This action is non-final.					
3) Since this application is in condition for alloward closed in accordance with the practice under the condition of the condition.					
Disposition of Claims					
4) ☐ Claim(s) 1-3,5,6,37-43,48 and 49 is/are pendi 4a) Of the above claim(s) is/are withdra 5) ☐ Claim(s) 1-3,5,6,37-43,48 and 49 is/are allowe 6) ☐ Claim(s) is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/o	own from consideration. ed.				
Application Papers					
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) acc Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the E	cepted or b) objected to be drawing(s) be held in abeyand cition is required if the drawing(ce. See 37 CFR 1.85(a). s) is objected to. See 37 CFR 1.121(d).			
Priority under 35 U.S.C. §§ 119 and 120					
12) Acknowledgment is made of a claim for foreig a) All b) Some * c) None of: 1. Certified copies of the priority documen 2. Certified copies of the priority documen 3. Copies of the certified copies of the priority application from the International Burea * See the attached detailed Office action for a list 13) Acknowledgment is made of a claim for domest since a specific reference was included in the fir 37 CFR 1.78. a) The translation of the foreign language pn 14) Acknowledgment is made of a claim for domest reference was included in the first sentence of the company to the foreign language pn	ts have been received. ts have been received in Apority documents have been to (PCT Rule 17.2(a)). t of the certified copies not be priority under 35 U.S.C. arst sentence of the specification has be tic priority under 35 U.S.C.	pplication No received in this National Stage received. § 119(e) (to a provisional application) ation or in an Application Data Sheet. een received. §§ 120 and/or 121 since a specific			
Attachment(s)	_				
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449) Paper No(s) 		ummary (PTO-413) Paper No(s) formal Patent Application (PTO-152)			

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DETAILED ACTION

- 1. The cancellation of claims 4, 7, and 44-47 is acknowledged.
- 2. The rejection of claims 1-3, 5, 6, 37, 40-43, 48 and 49 in paper mailed on 07/08/2003 is withdrawn in order to include a rejection of the above-mentioned claims and of claims 38 and 39.
- 3. Claims 1-3, 5, 6, 37-43, 48 and 49 are pending in the application.

Claim Objections

4. Claim 3 is objected to because of the following informalities: where claim 3 recites, "...metal nitrade..." should recite, "...metal nitride...". Appropriate correction is required.

Claim Rejections - 35 USC § 103

- 5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 6. Claims 1-3, 5, 6 and 37-41 are rejected under 35 U.S.C. 103(a) as being unpatentable over Stevens (U.S. 5,070,036) in view of Hoshino (U.S. 4,910,169).

In reference to claims 1-3, 5, 6, 40 and 41, Stevens (Fig.1) teaches an interconnecting semiconductor device comprising an opening part (3) formed in an insulating layer (2) on a substrate (1); a barrier layer (6) covering said opening part (3); a metal growth promoting layer (7) formed directly on said barrier layer (6), wherein said metal growth promoting layer comprises titanium nitride containing a lower oxygen

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concentration than said barrier layer (6) and is different from said first material; and an electroconductive layer (8, 9) comprising aluminum embedded in said opening part (3) or said depressed part via said barrier layer (6) and said metal growth promoting layer (7), wherein said electroconductive layer (8, 9) being formed directly on said metal growth promoting layer (7) and wherein said barrier layer (6) and said growth promoting layer (7) comprises a ground layer comprising titanium nitride containing oxygen at a high concentration at a lower part and at a low concentration in the upper part thereof (column 6, line 66 – column 11, line 61).

Stevens fails to teach the embedded electroconductive layer being formed of a Cu layer, an Al layer, or an Al alloy layer having Al as a main component; and selecting the barrier layer from the group consisting of WN_x and TaN_x , wherein x is a variable such that $0 \le x \ge 1$; However, Hoshino (Fig.1A) in a related art to the formation of an interconnect structure comprising an opening part (12a) formed in an insulation layer (12) on a substrate (10); a barrier layer (16) formed in said opening part (12a), wherein said barrier layer selected from the group consisting of WN_x and TaN_x, wherein x is a variable such that $0 \le x \ge 1$; and forming an electroconductive layer (18) comprising copper (column 2, line 65 - column 3, line 18). It would have been within the scope of one of ordinary skill in the art to combine the teachings of Stevens and Hoshino to enable replacing the barrier layer and the conductive layer of Stevens with those of Hoshino because one of ordinary skill in the art at the time the invention was made would have been motivated to look to alternative suitable materials disclosed in Stevens

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and art recognized suitability for an intended purpose has been recognized to be motivation to combine. MPEP 2144.07.

In reference to claims 37-39, the combined teachings of Stevens and Hoshino fail to teach wherein the metal growth promoting layer has a thickness of about 10-20 nm and wherein said barrier layer has a thickness of at least approximately 10 nm. Notwithstanding, it would have been an obvious matter of design choice bounded by well known manufacturing constraints and ascertainable by routine experimentation and optimization to choose these particular dimensions because applicant has not disclosed that the dimensions are for a particular unobvious purpose, produce an unexpected result, or are otherwise critical, and it appears prima facie that the process would possess utility using another dimension. Indeed, it has been held that mere dimensional limitations are prima facie obvious absent a disclosure that the limitations are for a particular unobvious purpose, produce an unexpected result, or are otherwise critical. See, for example, In re Rose, 220 F.2d 459, 105 USPQ 237 (CCPA 1955); In re Rinehart, 531 F.2d 1048, 189 USPQ 143 (CCPA 1976); Gardner v. TEC Systems, Inc., 725 F.2d 1338, 220 USPQ 777 (Fed. Cir. 1984), cert. denied, 469 U.S. 830, 225 USPQ 232 (1984); In re Dailey, 357 F.2d 669, 149 USPQ 47 (CCPA 1966).

7. Claim 42 is rejected under 35 U.S.C. 103(a) as being unpatentable over Stevens ('036) in view of Hoshino ('169) as applied to claims 1-3, 5, 6 and 37-41 above, and further in view of Lee (U.S. 5,552,341).

The combined teachings of Stevens and Hoshino fail to disclose the barrier layer comprising TiSiN. However, Lee (Fig.9) teaches an interconnect device including a

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barrier layer comprising TiSiN (column 10, lines 6-24). It would have been within the scope of one of ordinary skill in the art to combine the teachings of Stevens and Hoshino and Lee to enable replacing the barrier layer of Stevens and Hoshino with that of Lee because one of ordinary skill in the art at the time the invention was made would have been motivated to look to alternative suitable materials disclosed in Stevens and Hoshino and art recognized suitability for an intended purpose has been recognized to be motivation to combine. MPEP 2144.07, and furthermore because this would improve the step coverage of the metallic interconnect (column 8, lines 13-24).

Claims 43, 48 and 49 is rejected under 35 U.S.C. 103(a) as being unpatentable 8. over Stevens ('036) in view of Hoshino ('169) as applied to claims 1-3, 5, 6 and 37-41 above, and further in view of Mu et al. (U.S. 5,612,254).

In reference to claim 43, the combined teachings of Stevens and Hoshino fail to disclose a diffusion barrier comprising Al₂O₃. However, Mu et al. teach an interconnect structure comprising a barrier layer (not shown) comprising aluminum oxide and an electroconductive layer selected from the group comprising copper and aluminum (column 4, lines 38-55). It would have been within the scope of one of ordinary skill in the art to combine the teachings of Stevens and Hoshino with Mu et al. to replace the barrier layer of Stevens and Hoshino according to the teachings of Mu et al. because one of ordinary skill in the art at the time the invention was made would have been motivated to look to alternative suitable materials disclosed in Stevens and Hoshino and art recognized suitability for an intended purpose has been recognized to be motivation to combine. MPEP 2144.07.

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In reference to claims 48 and 49, the combined teachings of Stevens and Hoshino teach wherein the metal growth promoting layer is titanium nitride (Stevens, column 8, lines 2 and 3), wherein said titanium nitride is formed by reactive sputtering (Stevens, column 10, lines 60 – 65). The combined teachings of Stevens and Hoshino fail to teach wherein a chemical vapor deposition process forms said titanium nitride. However, Mu et al. teach forming titanium nitride layers using either sputtering or a chemical vapor deposition process (column 4,lines 42 – 55). It would have been within the scope of one of ordinary skill in the art to combine the teachings of Stevens and Hoshino with the teachings of Mu et al. to enable the titanium nitride of Stevens and Hoshino to be formed according to the teachings of Mu et al. because one of ordinary skill in the art at the time the invention was made would have been motivated to look to alternative suitable methods of forming the disclosed titanium nitride of Stevens and Hoshino and art recognized suitability for an intended purpose has been recognized to be motivation to combine. MPEP 2144.07.

Conclusion

Papers related to this application may be submitted directly to Art Unit 2823 by facsimile transmission. Papers should be faxed to Art Unit 2823 via the Art Unit 2823 Fax Center located in Crystal Plaza 4, room 3C23. The faxing of such papers must conform to the notice published in the Official Gazette, 1096 OG 30 (15 November 1989). The Art Unit 2823 Fax Center number is (703) 305-3432. The Art Unit 2823 Fax Center is to be used only for papers related to Art Unit 2823 applications.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Julio J. Maldonado at (703) 306-0098 and between the hours of 8:00 AM to 4:00 PM (Eastern Standard Time) Monday through Friday or by email via julio.maldonado@uspto.gov. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri, can be reached on (703) 306-2794.

Any inquiry of a general nature or relating to the status of this application should be directed to the Group 2800 Receptionist at (703) 308-0956.

JMR 1/10/04